Elektronische Bauelemente

2SA727

-3A, -40V

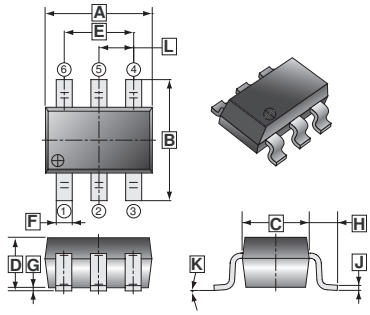
PNP Silicon General Purpose Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen and lead free

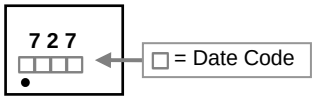
FEATURES

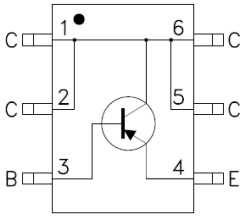
- High current output up to -3A
- Low saturation voltage

TSOP-6



MARKING





REF.	Millimeter Min.	Millimeter Max.	REF.	Millimeter Min.	Millimeter Max.
A	2.70	3.10	G	0	0.10
B	2.60	3.00	H	0.60 REF.	
C	1.40	1.80	J	0.12 REF.	
D	1.10 MAX.		K	0°	10°
E	1.90 REF.		L	0.95 REF.	
F	0.30	0.50			

PACKAGE INFORMATION

Package	MPQ	Leader Size
TSOP-6	3K	7' inch

ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Currrent	I_C	-3	A
Total Power Dissipation @ T_C=25°C [3]	P_D	1.2	W
Thermal Resistance Junction-ambient Max [1]	$R_{\theta JC}$	105	°C/W
Junction & Storage Temperature	T_J, T_{STG}	150, -55 ~ 150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25℃ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector-base breakdown voltage	$V_{(BR)CBO}$	-40	-	-	V	I_C= -100μA, I_E=0
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	-30	-	-	V	I_C= -1mA, I_B=0
Emitter-base breakdown voltage	$V_{(BR)EBO}$	-5	-	-	V	I_E= -10μA, I_C=0
Collector cut-off current	I_{CBO}	-	-	-0.1	μA	V_{CB}= -30V, I_E=0
Emitter cut-off current	I_{EBO}	-	-	-0.1	μA	V_{EB}= -5V, I_C=0
Collector-emitter saturation voltage [2]	$V_{CE(sat)}$	-	-0.15	-0.25	V	I_C= -0.5A, I_B= -5mA
		-	-0.85	-1		I_C= -2A, I_B= -20mA
		-	-0.25	-0.5		I_C= -2A, I_B= -200mA
Base-emitter saturation voltage [2]	$V_{BE(sat)}$	-	-0.8	-1.1	V	I_C= -0.5A, I_B= -5mA
		-	-1	-1.5		I_C= -2A, I_B= -200mA
DC current gain[2]	h_{FE}	30	-	-		V_{CE}= -2V, I_C= -20mA
		160	-	320		V_{CE}= -2V, I_C= -1A
Transition frequency	f_T	-	80	-	MHz	V_{CE}= -5V, I_C= -100mA, f=100MHz
Collector output capacitance	C_{ob}	-	55	-	pF	V_{CB}= -10V, f=1MHz

NOTE:

1. surface mounted on a 1 inch2 FR-4 board with 2OZ copper. , 167℃/W when mounted on Min. copper pad.
2. The data tested by pulsed , pulse width≦300us , duty cycle ≦2%
3. The power dissipation is limited by 150 ℃junction temperature

Elektronische Bauelemente

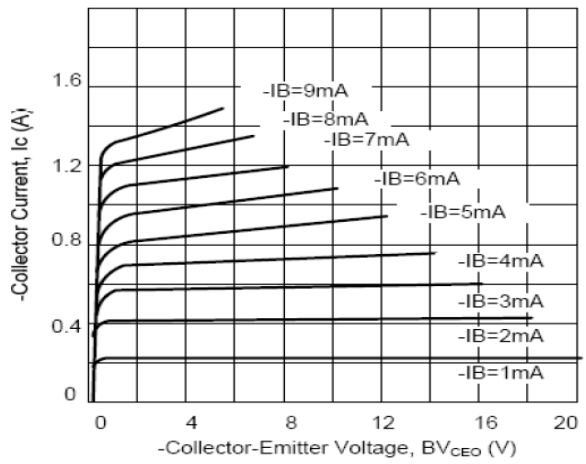
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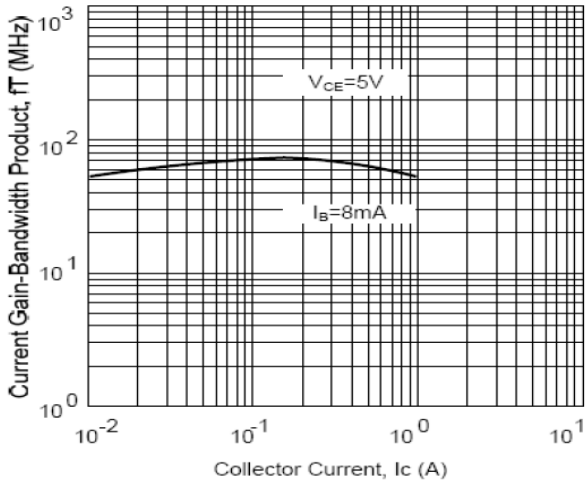
PNP Silicon General Purpose Transistor

CHARACTERISTIC CURVES

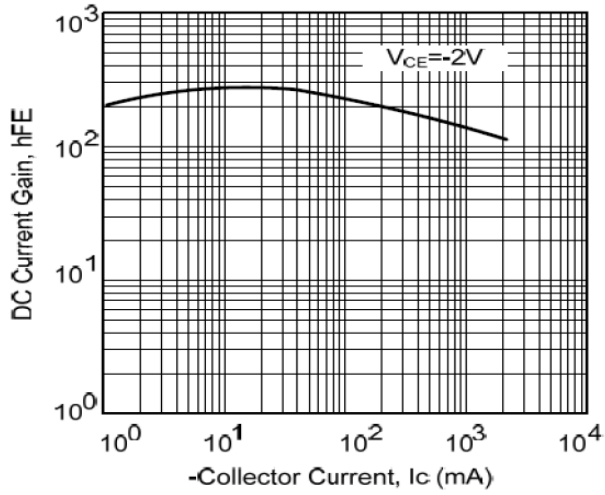
Static Characteristics



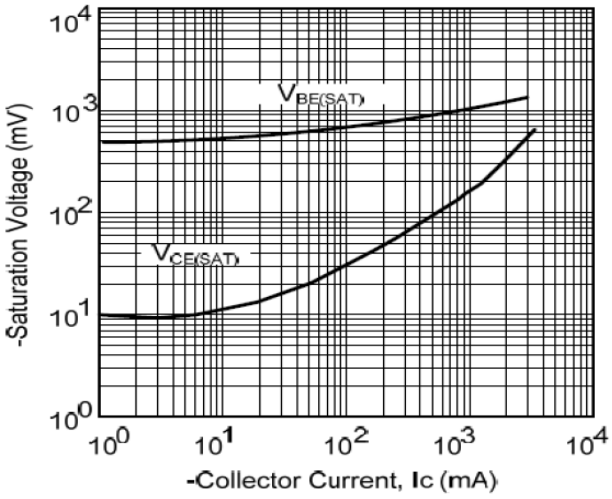
Current Gain-Bandwidth Product



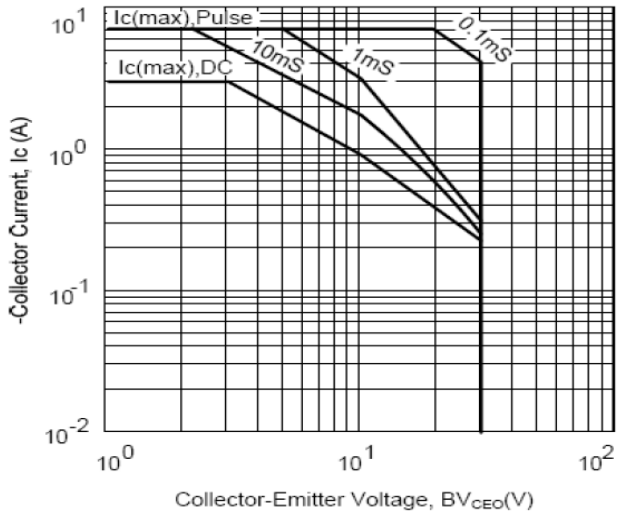
DC Current Gain



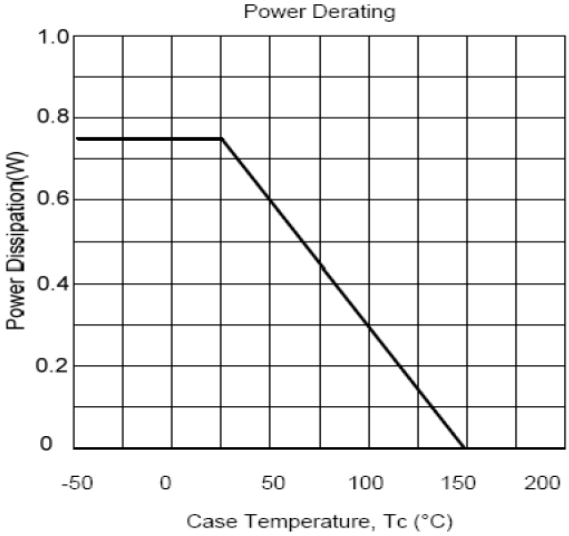
Saturation Voltage



Safe Operating Area



Power Derating



http://www.SeCoSGmbH.com/ Any changes of specification will not be informed individually.